IN THE CLAIMS:

Please find below a listing of all pending claims. The statuses of the claims are set forth in parentheses.

1. (Currently Amended): A semiconductor device fabrication method comprising the steps of:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while ~~a first polishing material~~ only a polishing slurry is supplied onto the polishing pad to thereby planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with the polishing pad while ~~a second polishing material is~~ said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,

wherein ~~said first polishing material comprises a~~ said polishing slurry ~~comprising~~ comprises abrasive grains and a surfactant additive[[,]]

~~wherein said second polishing material comprises said polishing slurry and water, and~~

~~wherein said first polishing material is different from said second polishing material~~.

2. (Currently Amended): A semiconductor device fabrication method comprising the steps of:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while ~~a first polishing material~~ only a polishing slurry is supplied onto the polishing pad to thereby planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with the polishing pad while ~~a second polishing material~~ a mixture of said polishing slurry and water is supplied onto the polishing pad, ~~the polishing slurry contained in the second polishing material being the same kind as the polishing slurry of the first polishing material,~~

wherein ~~said first polishing material comprises a~~ said polishing slurry ~~comprising~~ comprises abrasive grains and a surfactant additive, and

~~wherein said second polishing material comprises a mixture of said polishing slurry and water, and~~

~~wherein said first polishing material is different from said second polishing material~~

wherein a water content in said mixture of said polishing slurry and said water is higher than a water content in said polishing slurry.

3. (Currently Amended): A semiconductor device fabrication method comprising the steps of:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while ~~a first polishing material~~ only a polishing slurry is supplied onto the polishing pad to thereby planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with the polishing pad while ~~a second polishing material is~~ said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,

wherein ~~said first polishing material comprises a~~ said polishing slurry ~~comprising~~ comprises abrasive grains and a surfactant additive, and

~~wherein said second polishing material comprises said polishing slurry and water,~~

~~wherein said first polishing material is different from said second polishing material, and~~

wherein in the step of further polishing the surface of the film-to-be-polished, the water is supplied to a position outer of a position for [[the]] said polishing slurry to be supplied to.

4. (Currently Amended): A semiconductor device fabrication method comprising the steps of:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while ~~a first polishing material~~ only a polishing slurry is supplied onto the polishing pad to thereby planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with the polishing pad while ~~a second polishing material is~~ said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,

wherein ~~said first polishing material comprises a~~ said polishing slurry ~~comprising~~ comprises abrasive grains and a surfactant additive, and

~~wherein said second polishing material comprises said polishing slurry and water,~~

~~wherein said first polishing material is different from said second polishing material, and~~

wherein in the step of further polishing the surface of the film-to-be-polished, a supply amount of the water is 2 or more times as much as a supply amount of [[the]] said polishing

slurry.

5-11 (Cancelled)

12. (Original): A semiconductor device fabrication method according to claim 1, further comprising, before the step of planarizing the surface of the film-to-be-polished, the steps of:

forming over the semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,

in the step of further polishing the surface of the film-to-be-polished, the surface of the film-to-be-polished is polished with the insulation film as a stopper.

13. (Original): A semiconductor device fabrication method according to claim 2, further comprising, before the step of planarizing the surface of the film-to-be-polished, the steps of:

forming over the semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in

the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,

in the step of further polishing the surface of the film-to-be-polished, the surface of the film-to-be-polished is polished with the insulation film as a stopper.

14-27 (Cancelled)

28. (Original): A semiconductor device fabrication method according to claim 1, wherein

the abrasive grains comprise cerium oxide or silicon oxide,

the additive comprises poly(ammonium acrylate).

29. (Original): A semiconductor device fabrication method according to claim 2, wherein

the abrasive grains comprise cerium oxide or silicon oxide,

the additive comprises poly(ammonium acrylate).

30-33 (Cancelled)

34. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

~~the ratio of~~ in the step of further polishing the surface of the film-to-be-polished, a supply amount of ~~the second polishing material of the~~ said polishing slurry to a supply amount of [[the]]

said water is 1:5.